AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

1-24.(canceled)

25.(new) A negative-resistance circuit having a transistor and distributed constant lines respectively connected to three terminals thereof, said negative-resistance circuit characterized by comprising:

an inductance element connected between an output terminal of said negative-resistance circuit and a ground potential for adjusting a negative resistance value; and

a plurality of distributed constant lines connected in parallel to at least one of the three terminals of said transistor.

26.(new) The negative-resistance circuit according to claim 25, wherein:

said inductance element comprises a distributed constant line shorter than one-quarter wavelength at a desired frequency for connecting between a signal conductor and the ground potential.

27.(new) The negative-resistance circuit according to claim 25, wherein:

said distributed constant line is a coplanar type one composed of a signal conductor and ground conductors disposed to sandwich said signal conductor with predetermined gaps therebetween, and

said inductance element comprises a conductor piece which traverses only one of said gaps to connect said signal conductor with said ground conductor.

28.(new) A negative-resistance circuit having a transistor and distributed constant lines respectively connected to three terminals thereof, said negative-resistance circuit characterized by comprising:

a capacitance element connected between an output terminal of said negative-resistance circuit and a ground potential for adjusting a negative resistance value,

a plurality of distributed constant lines connected in parallel to at least one of the three terminals of said transistor.

29.(new) The negative-resistance circuit according to claim 28, wherein:

said capacitance element comprises a distributed constant line which is branched from a signal conductor, has an opened leading end, and is shorter than one-quarter wavelength at a desired frequency.

30.(new) The negative-resistance circuit according to claim 28, wherein:

said distributed constant line is a coplanar type one composed of a signal conductor and ground conductors disposed to sandwich said signal conductor with predetermined gaps therebetween, and

said capacitance element comprises a conductor piece which is branched from said signal conductor and has an opened leading end.

31.(new) A negative-resistance circuit having a transistor and distributed constant lines respectively connected to three terminals thereof, said negative-resistance circuit characterized in that:

a plurality of distributed constant lines are connected in parallel to at least one of the three terminals of said transistor.

32.(new) The negative-resistance circuit according to claim 25, wherein:

one of said plurality of distributed constant lines connected in parallel is a distributed constant line which is longer than one-quarter wavelength and shorter than one-half wavelength at a desired frequency, and has a leading end connected to a ground potential.

33.(new) The negative-resistance circuit according to claim 25, wherein:

one of said plurality of distributed constant lines connected in parallel is a distributed constant line which is shorter than one-quarter wavelength at a desired frequency, and has an opened leading end, and

the remaining distributed constant lines are distributed constant lines each having a leading end short-circuited to a ground potential.

34.(new) The negative-resistance circuit according to claim 28, wherein:

one of said plurality of distributed constant lines connected in parallel is a distributed constant line which is longer than one-quarter wavelength and shorter than one-half wavelength at a desired frequency, and has a leading end connected to a ground potential.

35.(new) The negative-resistance circuit according to claim 28, wherein:

one of said plurality of distributed constant lines connected in parallel is a distributed constant line which is shorter than one-quarter wavelength at a desired frequency, and has an opened leading end, and

the remaining distributed constant lines are distributed constant lines each having a leading end short-circuited to a ground potential.

36.(new) The negative-resistance circuit according to claim 31, wherein:

one of said plurality of distributed constant lines connected in parallel is a distributed constant line which is longer than one-quarter wavelength and shorter than one-half

wavelength at a desired frequency, and has a leading end connected to a ground potential.

37.(new) The negative-resistance circuit according to claim 31, wherein:

one of said plurality of distributed constant lines connected in parallel is a distributed constant line which is shorter than one-quarter wavelength at a desired frequency, and has an opened leading end, and

the remaining distributed constant lines are distributed constant lines each having a leading end short-circuited to a ground potential.

38.(new) The negative-resistance circuit according to claim 25, wherein:

said transistor is a field effect transistor, and

said terminal to which said plurality of distributed constant lines are connected in parallel is a source of said field effect transistor.

39.(new) The negative-resistance circuit according to claim 28, wherein:

said transistor is a field effect transistor, and

said terminal to which said plurality of distributed constant lines are connected in parallel is a source of said field effect transistor.

40.(new) The negative-resistance circuit according to claim 31, wherein:

said transistor is a field effect transistor, and

said terminal to which said plurality of distributed constant lines are connected in parallel is a source of said field effect transistor.

41.(new) The negative-resistance circuit according to claim 38, wherein:

an output terminal of said negative-resistance circuit is disposed through a distributed constant line connected to a gate of said field effect transistor, wherein:

said negative-resistance circuit comprises:

a bias power source for supplying said gate with a predetermined DC voltage; and

a resistor connected between said bias power source and said distributed constant line connected to said gate.

42.(new) The negative-resistance circuit according to claim 39, wherein:

an output terminal of said negative-resistance circuit is disposed through a distributed constant line connected to a gate of said field effect transistor, wherein:

said negative-resistance circuit comprises:

a bias power source for supplying said gate with a predetermined DC voltage; and

a resistor connected between said bias power source and said distributed constant line connected to said gate.

43.(new) The negative-resistance circuit according to claim 40, wherein:

an output terminal of said negative-resistance circuit is disposed through a distributed constant line connected to a gate of said field effect transistor, wherein:

said negative-resistance circuit comprises:

a bias power source for supplying said gate with a predetermined DC voltage; and

a resistor connected between said bias power source and said distributed constant line connected to said gate.

44.(new) An active filter comprising:

the negative-resistance circuit according to claim 25; and

a resonator connected in series with said negative-resistance circuit.

45.(new) An active filter comprising:

the negative-resistance circuit according to claim 28; and

a resonator connected in series with said negative-resistance circuit.

46.(new) An active filter comprising:

the negative-resistance circuit according to claim 31; and

a resonator connected in series with said negative-resistance circuit.